

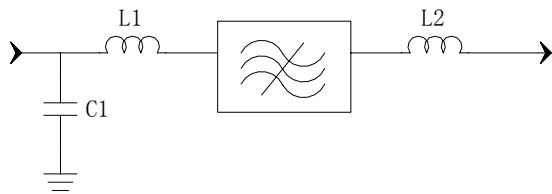
Specifications

Parameter	Unit	Minimum	Typical	Maximum
Center Frequency	MHz	119.9	120	120.1
Insertion Loss	dB		23	24.5
3dB Bandwidth	MHz	20.4	20.6	
50 dB Bandwidth	MHz		22.1	22.4
Passband Variation	dB		0.8	1.2
Absolute Delay	usec		2.14	
Ultimate Rejection	dB	50	55	
Substrate Material		128 LiNbO ₃		
Ambient Temperature	°C	25		
Package Size		DIP2212 (22.2x12.8x4.7mm ³)		

Notes:

1. All specifications are based on the test circuit shown
2. In production, devices will be tested at room temperature to a guardbanded specification to ensure electrical compliance over temperature
3. Electrical margin has been built into the design to account for the variations due to temperature drift and manufacturing tolerances
4. This is the optimum impedance in order to achieve the performance show

Matching Configuration



L1 = 39nH L2 = 33nH

C1 = 30pF

Source/Load Impedance = 50 ohm

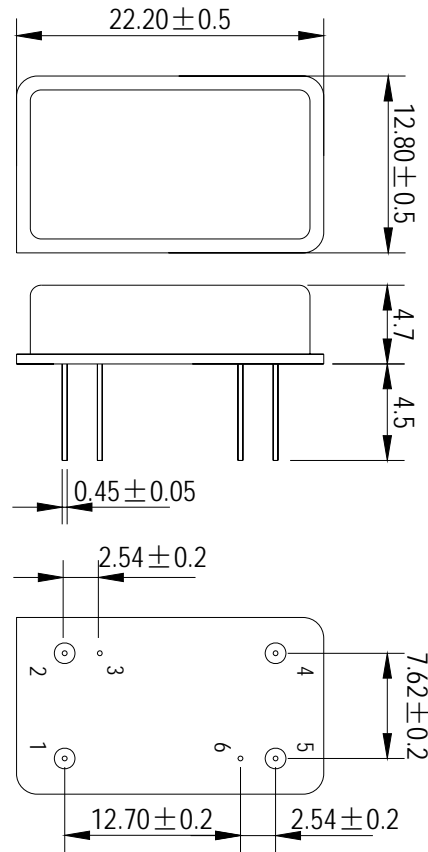
Notes - Component values may change depending on board layout.



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Part Number	LBN12015		
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Package Dimension



Pin 1: input
Pin 5: output
Others: Grounded

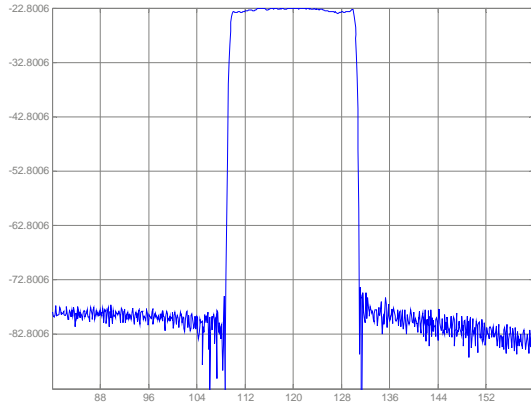


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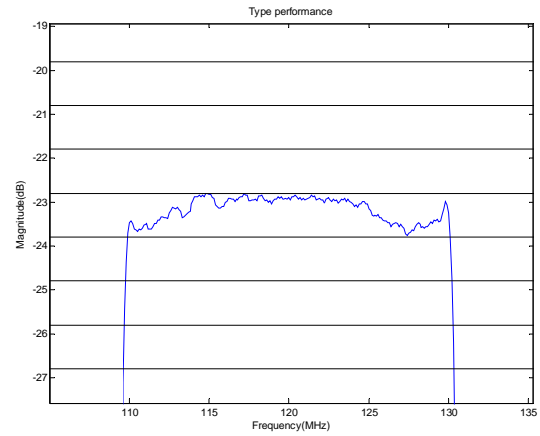
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Typical Performance

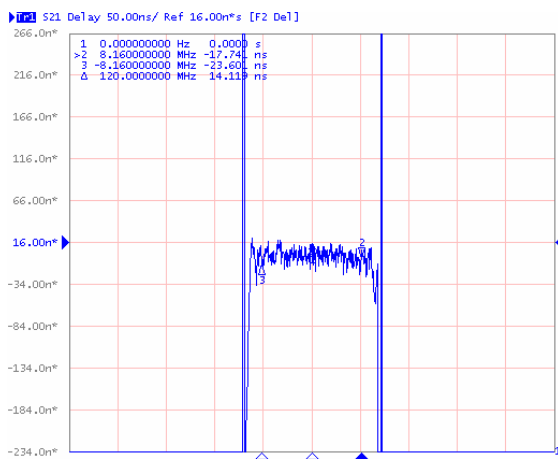
Frequency Respond



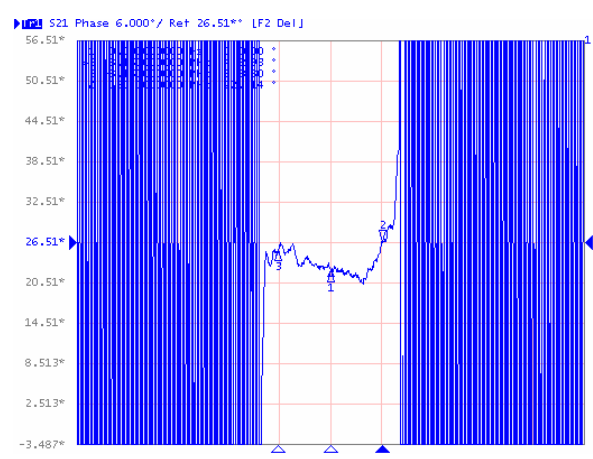
Passband Respond



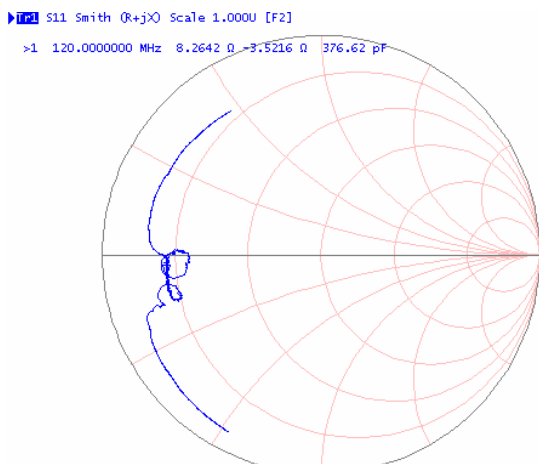
Group Delay Variation($f_0 \pm 8.16\text{MHz}$)



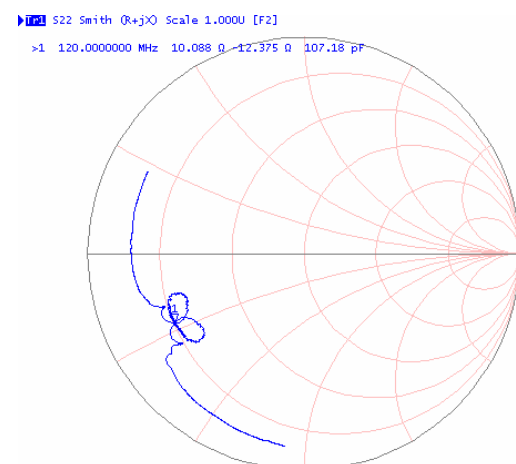
Phase Linearity($f_0 \pm 8.16\text{MHz}$)



Simth Chart S11



Simth Chart S22



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